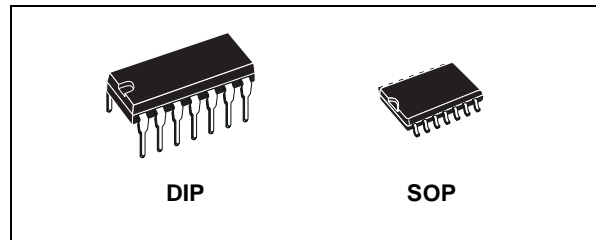




HCF4011B

QUAD 2 INPUT NAND GATE

- PROPAGATION DELAY TIME
 $t_{PD} = 60\text{ns}$ (Typ.) at $V_{DD} = 10\text{V}$
- BUFFERED INPUTS AND OUTPUTS
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT
 $I_1 = 100\text{nA}$ (MAX) AT $V_{DD} = 18\text{V}$ $T_A = 25^\circ\text{C}$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



ORDER CODES

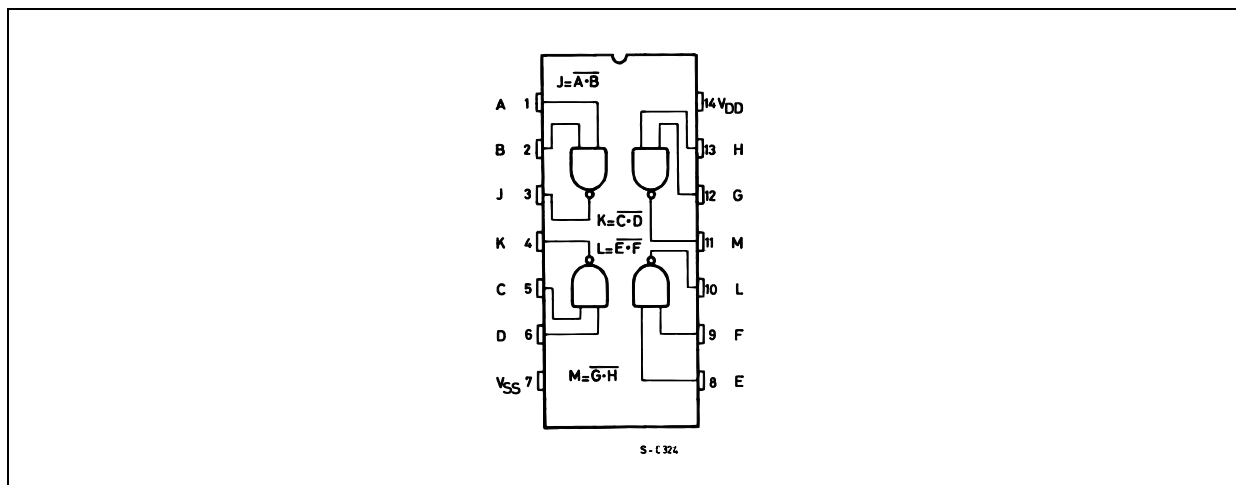
PACKAGE	TUBE	T & R
DIP	HCF4011BEY	
SOP	HCF4011BM1	HCF4011M013TR

DESCRIPTION

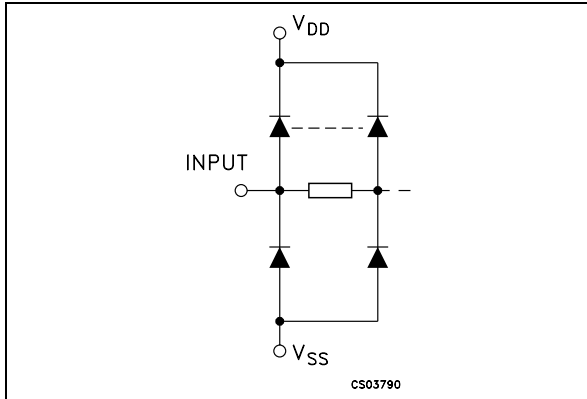
The HCF4011B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The HCF4011B QUAD 2 INPUT NAND GATE provides the system designer with direct

implementation of the NAND function and supplement the existing family of CMOS gates. All inputs and outputs are buffered.

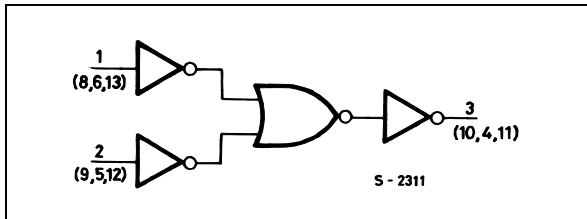
PIN CONNECTION



INPUT EQUIVALENT CIRCUIT



LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 5, 6, 8, 9, 12, 13	A, B, C, D, E, F, G, H	Data Inputs
3, 4, 10, 11	J, K, L, M	Data Outputs
7	V _{SS}	Negative Supply Voltage
14	V _{DD}	Positive Supply Voltage

TRUTH TABLE

INPUTS		OUTPUTS
A, C, E, G	B, D, F, H	J, K, L, M
L	L	H
L	H	H
H	L	H
H	H	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	-0.5 to +22	V
V _I	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	3 to 20	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value						Unit	
		V _I (V)	V _O (V)	I _{OL} (μ A)	V _{DD} (V)	T _A = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.		Max.
I _L	Quiescent Current	0/5			5		0.01	0.25		7.5		7.5	μ A
		0/10			10		0.01	0.5		15		15	
		0/15			15		0.01	1		30		30	
		0/20			20		0.02	5		150		150	
V _{OH}	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V _{OL}	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V _{IH}	High Level Input Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		V
			1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
V _{IL}	Low Level Input Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	V
			9/1	<1	10			3		3		3	
			13.5/1.5	<1	15			4		4		4	
I _{OH}	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I _{OL}	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I _I	Input Leakage Current	0/18	Any Input		18		$\pm 10^{-5}$	± 0.1		± 1		± 1	μ A
C _I	Input Capacitance		Any Input				5	7.5					pF

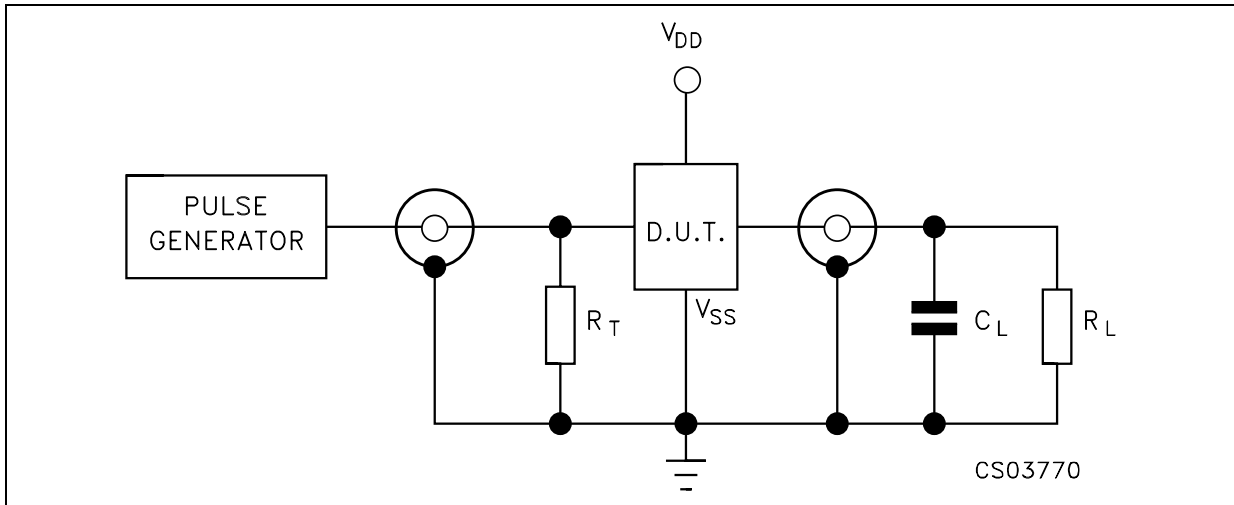
The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}=5V, 2V min. with V_{DD}=10V, 2.5V min. with V_{DD}=15V

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200K Ω , t_r = t_f = 20 ns)

Symbol	Parameter	Test Condition			Value (*)			Unit
		V _{DD} (V)			Min.	Typ.	Max.	
t _{PLH} t _{PHL}	Propagation Delay Time	5				125	250	ns
		10				60	120	
		15				45	90	
t _{TLH} t _{THL}	Output Transition Time	5				100	200	ns
		10				50	100	
		15				40	80	

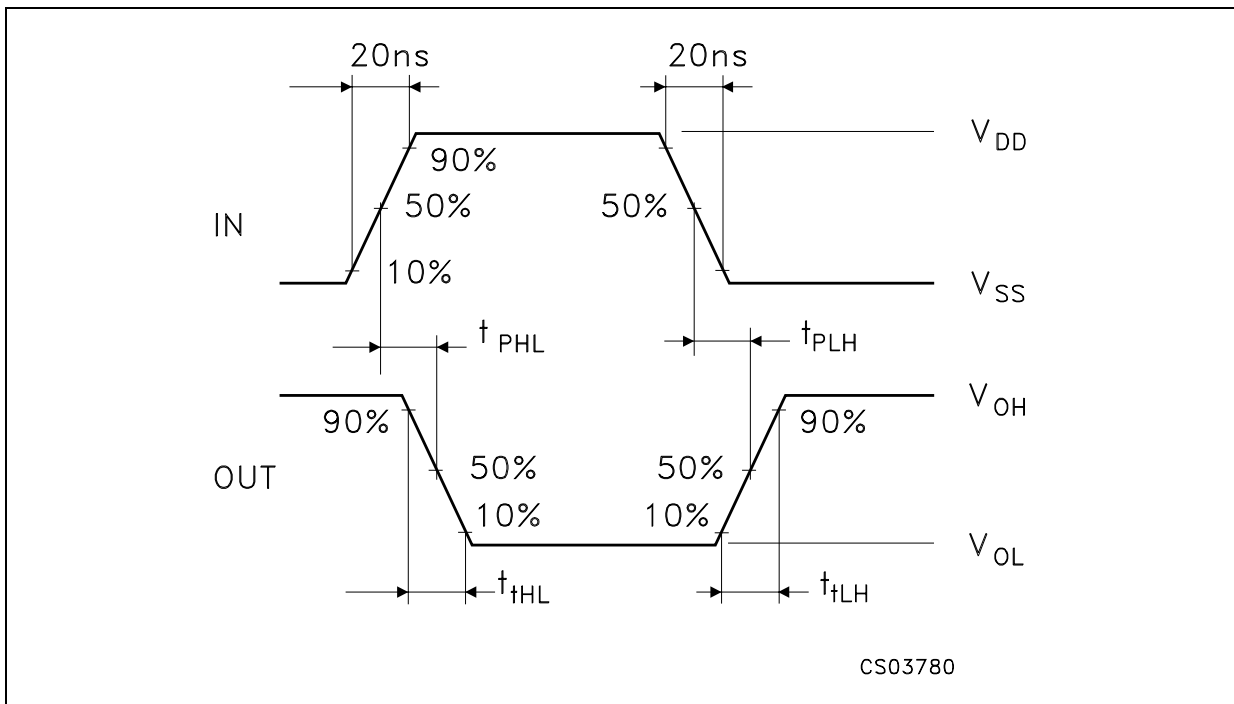
(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.

TEST CIRCUIT



$C_L = 50\text{pF}$ or equivalent (includes jig and probe capacitance)
 $R_L = 200\text{k}\Omega$
 $R_T = Z_{\text{OUT}}$ of pulse generator (typically 50Ω)

WAVEFORM : PROPAGATION DELAY TIMES ($f=1\text{MHz}$; 50% duty cycle)



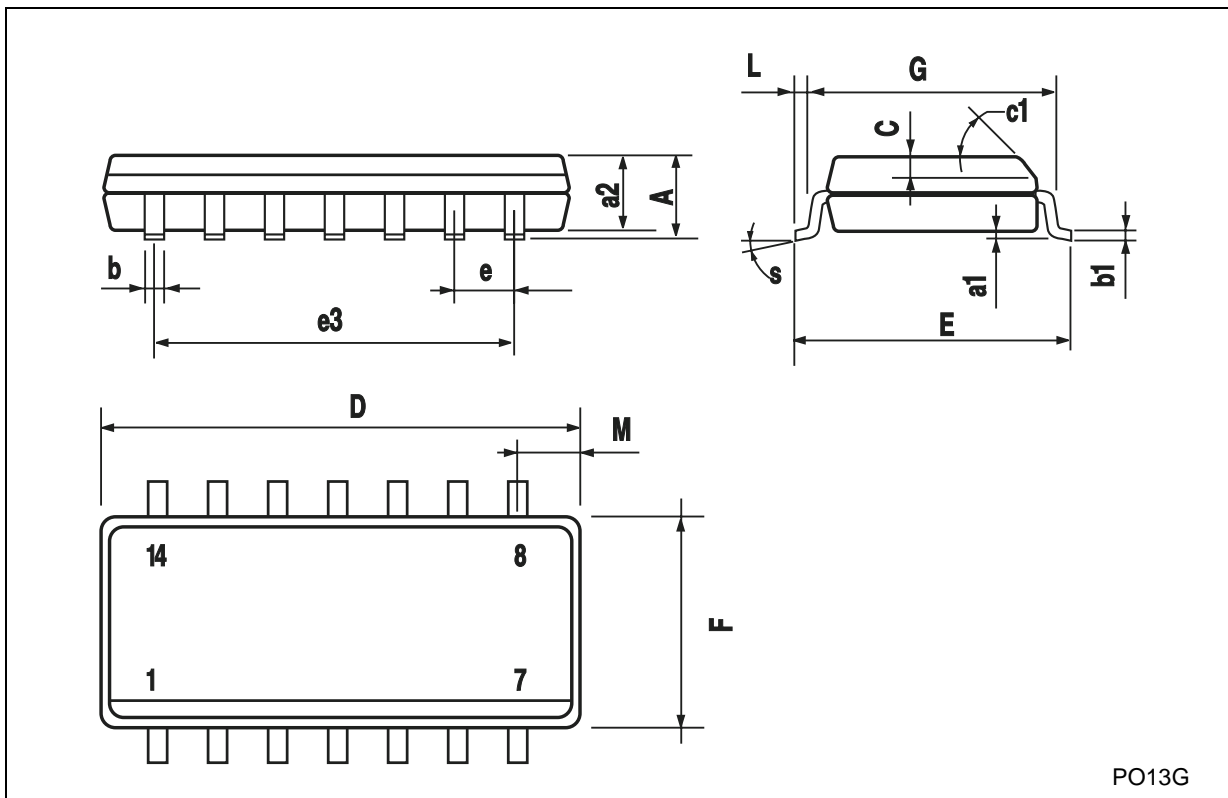
Plastic DIP-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

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